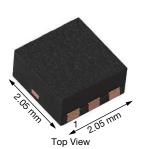


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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PowerPAK® SC-70-6L Single





Marking Code: QEXXXX

PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.035			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.050			
I _D (A)	-10			
Configuration	Single			
Package	PowerPAK SC-70			

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

G O	s T
P-Channel MOSFET	O D

ABSOLUTE MAXIMUM RATIN	GS (1 _C = 25 °C, unles	s otherwise noted	1)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-40	V
Gate-source voltage		V_{GS}	± 20	V
Continuous drain current	T _C = 25 °C	I _D	-10	
	T _C = 125 °C		-10	
Continuous source current (diode conduction) ^a		I _S	10	А
Pulsed drain current ^b		I _{DM}	-40	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-15	
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	11.25	mJ
Maximum power dissipation ^b	T _C = 25 °C	D	13.6	W
	T _C = 125 °C	P_{D}	4.5	VV
Operating junction and storage temperatu	re range	T _J , T _{stq}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	R _{thJA}	90	°C/W	
Junction-to-case (drain)		R_{thJF}	11	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		•				I.	·
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		-2.0	-2.5	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	μΑ
-		$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 175 °C	-	-	-150	1
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge 5 \text{ V}$	-8	-	-	Α
		V _{GS} = -10 V	I _D = -5 A	-	0.027	0.035	Ω
Duning and the second of the s	Б	V _{GS} = -10 V	I _D = -5 A, T _J = 125 °C	-	-	0.067	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -5 A, T _J = 175 °C	-	-	0.080	
		V _{GS} = -4.5 V	I _D = -4 A	-	0.038	0.050	
Forward transconductance b	9 _{fs}	$V_{DS} = -10 \text{ V}, I_{D} = -7 \text{ A}$		-	18	-	S
Dynamic ^b	·						
Input capacitance	C _{iss}			-	1450	1815	
Output capacitance	C _{oss}	$V_{GS} = 0 \text{ V}$ $V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$	-	105	131	рF	
Reverse transfer capacitance	C _{rss}			-	92	115	1
Total gate charge c	Q_g			-	26	33	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{GS} = -10 \text{ V}$ $V_{DS} = -20 \text{ V}, I_D = -8 \text{ A}$	-	4.1	-	nC
Gate-drain charge ^c	Q_{gd}			-	4.8	-	
Gate resistance	R _g	f = 1 MHz		4.4	7.4	11.8	Ω
Turn-on delay time ^c	t _{d(on)}			-	9	15	
Rise time ^c	t _r	V_{DD} = -20 V, R_L = 8 Ω $I_D \cong$ -2.5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	4	8	ns
Turn-off delay time ^c	t _{d(off)}			-	36	55	
Fall time ^c	t _f			-	10	16	
Source-Drain Diode Ratings and Char	acteristics						
Pulsed current ^a	I _{SM}			-	-	-40	Α
Forward voltage	V_{SD}	$I_F = -5 \text{ A}, V_{GS} = 0$			-0.84	-1.2	V

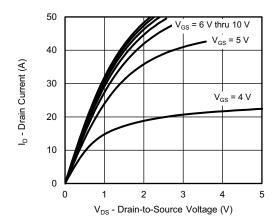
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

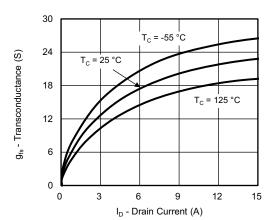
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



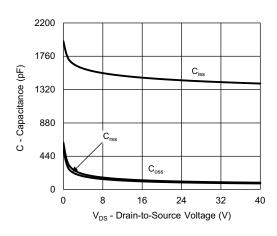
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



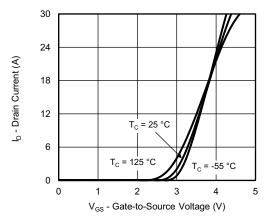
Output Characteristics



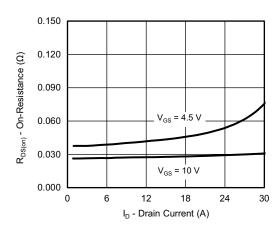
Transconductance



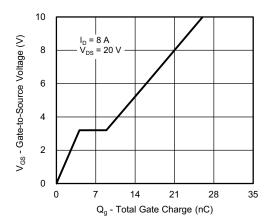
Capacitance



Transfer Characteristics



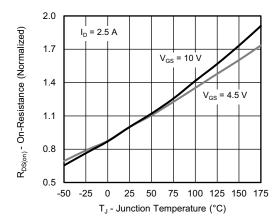
On-Resistance vs. Drain Current



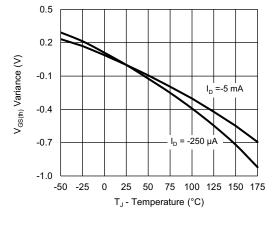
Gate Charge



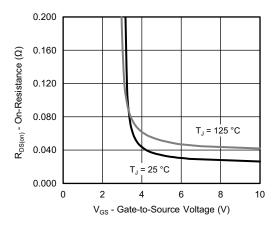
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



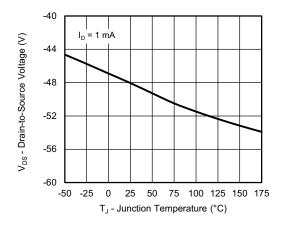
On-Resistance vs. Junction Temperature



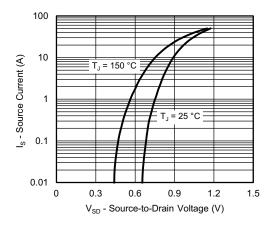
Threshold Voltage



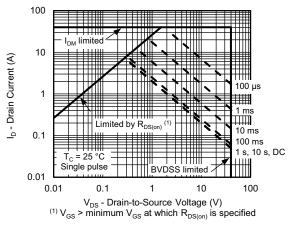
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



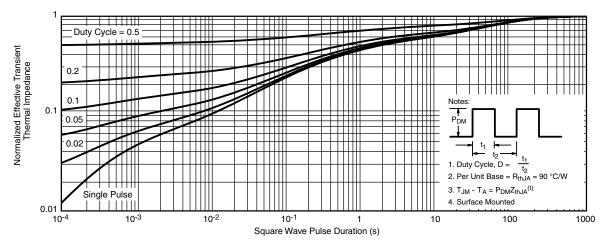
Source-Drain Diode Forward Voltage



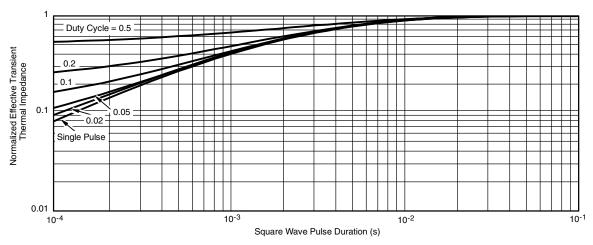
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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